

**Silicon PNP Power Transistors**

**2SB506**

**DESCRIPTION**

- With TO-3 package
- Wide area of safe operation

**APPLICATIONS**

- Low frequency power amplification
- Power switching application

**PINNING(see Fig.2)**

PIN	DESCRIPTION
1	Base
2	Emitter
3	Collector

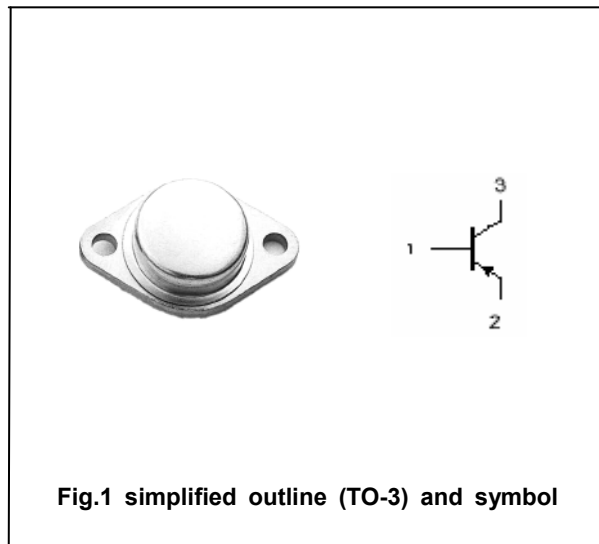


Fig.1 simplified outline (TO-3) and symbol

**Absolute maximum ratings(Ta=□)**

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V <sub>CBO</sub>	Collector-base voltage	Open emitter	-150	V
V <sub>CEO</sub>	Collector-emitter voltage	Open base	-100	V
V <sub>EBO</sub>	Emitter-base voltage	Open collector	-7	V
I <sub>C</sub>	Collector current		-5	A
P <sub>C</sub>	Collector power dissipation	T <sub>C</sub> =25□	60	W
T <sub>j</sub>	Junction temperature		100	□
T <sub>stg</sub>	Storage temperature		-55~100	□

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## CHARACTERISTICS

T<sub>j</sub>=25 °C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V <sub>(BR)CEO</sub>	Collector-emitter breakdown voltage	I <sub>C</sub> =-10mA; I <sub>B</sub> =0	-100			V
V <sub>(BR)EBO</sub>	Emitter-base breakdown voltage	I <sub>E</sub> =-1mA; I <sub>C</sub> =0	-7			V
V <sub>CEsat</sub>	Collector-emitter saturation voltage	I <sub>C</sub> =-5A; I <sub>B</sub> =-0.5A			-1.0	V
V <sub>BEsat</sub>	Base-emitter saturation voltage	I <sub>C</sub> =-5A; I <sub>B</sub> =-0.5A			-1.5	V
I <sub>CBO</sub>	Collector cut-off current	V <sub>CB</sub> =-100V; I <sub>E</sub> =0			-0.1	mA
I <sub>EBO</sub>	Emitter cut-off current	V <sub>EB</sub> =-7V; I <sub>C</sub> =0			-0.1	mA
h <sub>FE</sub>	DC current gain	I <sub>C</sub> =-1A; V <sub>CE</sub> =-5V	35		200	
f <sub>T</sub>	Transition frequency	I <sub>C</sub> =-0.3A; V <sub>CE</sub> =-10V		20		MHz

PACKAGE OUTLINE



Fig.2 outline dimensions (unindicated tolerance:±0.1mm)